

SOT-23 Formed SMD Package

**CMBTA13
CMBTA14**

N-P-N SMALL-SIGNAL DARLINGTON TRANSISTORS

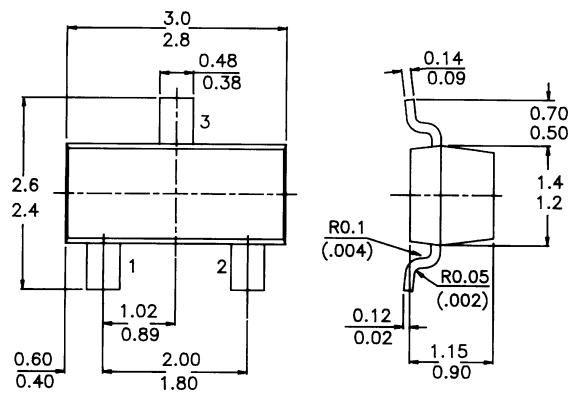
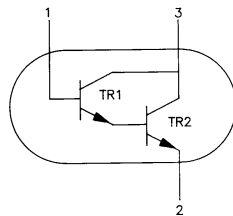
N-P-N transistors

Marking

CMBTA13 = 1M
CMBTA14 = 1N

PACKAGE OUTLINE DETAILS
ALL DIMENSIONS IN mm

Pin configuration
1 = BASE
2 = EMITTER
3 = COLLECTOR



ABSOLUTE MAXIMUM RATINGS

Collector-emitter voltage (open base)

$V_{BE} = 0$

Collector current (d.c.)

Total power dissipation up to $T_{amb} = 25^{\circ}C$

Junction temperature

D.C. current gain

$I_C = 10 \text{ mA}; V_{CE} = 5 \text{ V}$

Transition frequency at $f = 100 \text{ MHz}$

$I_C = 10 \text{ mA}; V_{CE} = 5 \text{ V}$

V_{CES}	max.	30 V
I_C	max.	300 mA
P_{tot}	max.	250 mW
T_j	max.	150 °C
CMBTA13 h_{FE}	min.	5000
CMBTA14 h_{FE}	min.	10000
f_T	min.	125 MHz

CMBTA13
CMBTA14

RATINGS (at $T_A = 25^\circ\text{C}$ unless otherwise specified)

Limiting values

Collector-base voltage (open emitter) $V_{BE} = 0$	V_{CBO}	max.	30 V
Collector-emitter voltage (open base) $V_{BE} = 0$	V_{CES}	max.	30 V
Emitter-base voltage (open collector)	V_{EBO}	max.	10 V
Collector current (d.c.)	I_C	max.	300 mA
Total power dissipation up to $T_{amb} = 25^\circ\text{C}$	P_{tot}	max.	250 mW
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$
Junction temperature	T_j	max.	150 $^\circ\text{C}$

THERMAL RESISTANCE

from junction to ambient	$R_{th\ j-a}$		500 K/W
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CHARACTERISTICS (at $T_A = 25^\circ\text{C}$ unless otherwise specified)

Collector-emitter breakdown voltage $I_C = 100\ \mu\text{A}$	$V_{(BR)CES}$	min.	30 V
Emitter-base cut-off current $V_{BE} = 10\ \text{V}$	I_{EBO}	max.	0.1 μA
Collector-base cut-off current $V_{CB} = 30\ \text{V}$	I_{CBO}	max.	0.1 μA
D.C. current gain $I_C = 10\ \text{mA}; V_{CE} = 5\ \text{V}$	CMBTA13 h_{FE}	min.	5000
	CMBTA14 h_{FE}	min.	10000
$I_C = 100\ \text{mA}; V_{CE} = 5\ \text{V}$	CMBTA13 h_{FE}	min.	10000
	CMBTA14 h_{FE}	min.	20000
Collector-emitter saturation voltage $I_C = 100\ \text{mA}; I_B = 0.1\ \text{mA}$	V_{CEsat}	max.	1.5 V
Base-emitter On voltage $I_C = 100\ \text{mA}; V_{CE} = 5\ \text{V};$	$V_{BE(on)}$	max.	2 V
Transition frequency at $f = 100\ \text{MHz}$ $I_C = 10\ \text{mA}; V_{CE} = 5\ \text{V}$	f_T	min.	125 MHz

Disclaimer

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